

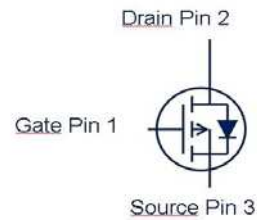
SIPMOS® Power-Transistor

Features

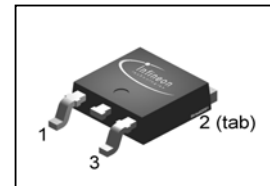
- P-Channel
- Enhancement mode
- Logic level
- Avalanche rated
- Pb-free lead plating; RoHS compliant

Product Summary

V_{DS}	-100	V
$R_{DS(on),max}$	850	mΩ
I_D	-4.2	A



PG-TO-252-3



Type	Package	Marking	Lead free	Packing
SPD04P10PL G	PG-TO252-3	04P10PL	Yes	Non dry

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
			steady state	
Continuous drain current	I_D	$T_C=25\text{ °C}$	-4.2	A
		$T_C=100\text{ °C}$	3.0	
		$T_C=25\text{ °C}$	-16.8	
Pulsed drain current	$I_{D,pulse}$	$T_C=25\text{ °C}$	-16.8	
Avalanche energy, single pulse	E_{AS}	$I_D=-4.2\text{ A}$, $R_{GS}=25\text{ Ω}$	57	mJ
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	38	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 175	°C
ESD class		JESD22-A114-HBM	1A (250 V to 500 V)	
Soldering temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/175/56	